

SOT-23 Plastic-Encapsulate Transistors**MMBT2907ALT1** TRANSISTOR (PNP)**FEATURES**

Power dissipation

$$P_{CM}: 0.3 \text{ W (Tamb=25°C)}$$

Collector current

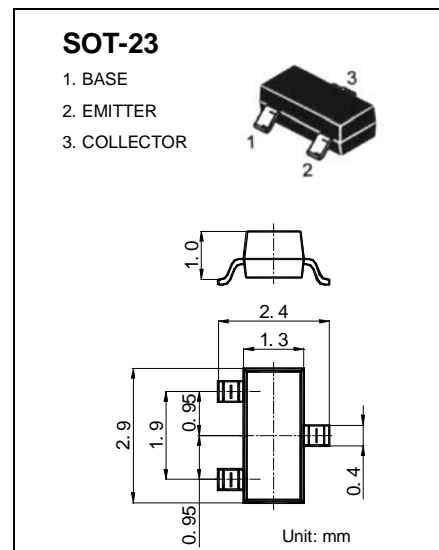
$$I_{CM}: -0.6 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO}: -60 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55°C \text{ to } +150°C$$

**ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10\mu A, I_E = 0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10 \text{ mA}, I_B = 0$	-60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu A, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -50V, I_E = 0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CB} = -3V, I_B = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -3V, I_C = 0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -10V, I_C = -150mA$	100		300	
	$h_{FE(2)}$	$V_{CE} = -10V, I_C = -1mA$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500mA, I_B = -50 \text{ mA}$			-1	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500mA, I_B = -50 \text{ mA}$			-2	V
Transition frequency	f_T	$V_{CE} = -20V, I_C = -50mA$ $f = 100MHz$	200			MHz

DEVICE MARKING:

MMBT2907ALT1 =2F